



CONFIDENTIAL

Patent
Attorney's Docket No. 033277-004

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of)
Nadim HADDAD et al) Group Art Unit: 2812
Application No.: 09/629,172) Examiner: R. Pompey
Filed: July 31, 2000)
For: METHOD TO HARDEN SHALLOW)
TRENCH ISOLATION AGAINST)
TOTAL IONIZING DOSE RADIATION)

#81B
12/10/01
V. Vannal

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SUPPLEMENTAL AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated July 6, 2001 and the Office Communication dated October 22, 2001, please amend the above-identified patent application as follows:

IN THE CLAIMS:

Please cancel claim 6 and substitute amended claims 1 and 7 as follows:

1. (Amended) A method for fabricating radiation-tolerant integrated circuit devices, said method comprising:
- depositing a layer of pad oxide on a semiconductor substrate;
 - selectively etching said pad oxide layer and said semiconductor substrate to define a trench within said semiconductor substrate;
 - implanting boron ions at an angle with respect to normal in said trench; and
 - implanting an electrically neutral material into said substrate.

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